



INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTORNEY'S DKT 015290-517	APPLICATION NO. 09/788,365
APPLICANT Tuqiang NI et al.	
FILING DATE February 21, 2001	GROUP 1763

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

Examiner Initials	Foreign Patent Document		Country	Date of Publication (MM-DD-YYYY)	Translation	
	Number	Kind Code (if known)			Yes	No

NON-PATENT LITERATURE DOCUMENTS

Examiner Initials	<p>Include name of author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.</p>

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Examiner Signature	Rudy Jennings	Date Considered	August 27, 2002
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